

Features

- Ultra small package: 1.0x0.6x0.5mm
- Very low capacitance: 0.35pF typical
- Ultra low leakage: nA level
- Low operating voltage: $\pm 5V$
- Low clamping voltage
- 3-pin leadless package
- Up to 2-line protects
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
Air discharge: $\pm 15kV$
Contact discharge: $\pm 8kV$
 - IEC61000-4-4 (EFT) 40A (5/50ns)
- RoHS Compliant

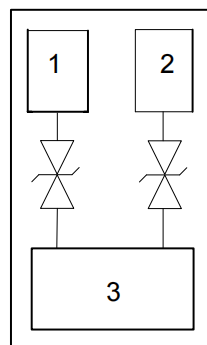
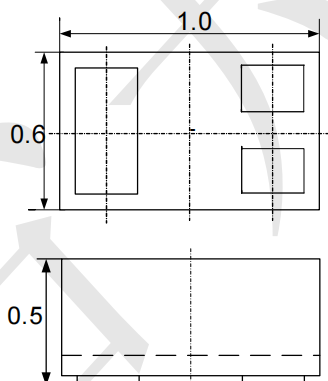
Mechanical Characteristics

- Package: DFN1006-3 (1.0x0.6x0.5mm)
- Lead Finish: NiPdAu
- Case Material: "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Shipping Qty : 10000pcs/7Inch Tape & Reel

Applications

- Cellular Handsets & Accessories
- Digital Visual Interface (DVI)
- Display Port
- MDDI Ports
- USB Ports
- PCI Express
- Serial ATA

Dimensions and Pin Configuration

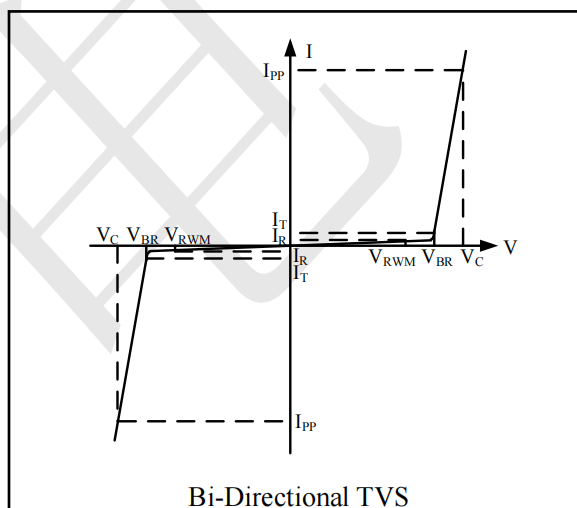


Absolute Maximum Ratings ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
ESD per IEC 61000-4-2 (Air)	VESD	± 15	kV
ESD per IEC 61000-4-2 (Contact)		± 8	
Operating Temperature Range	T_J	-55 to $+125$	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55 to $+150$	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter
V_{RWM}	Nominal Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Reverse Breakdown Voltage @ I_T
I_T	Test Current for Reverse Breakdown
V_C	Clamping Voltage @ I_{PP}
I_{PP}	Maximum Peak Pulse Current
C_{ESD}	Parasitic Capacitance
V_R	Reverse Voltage
f	Small Signal Frequency



Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			5	V	Pin 1 or pin 2 to pin 3 and between pin 1 and pin 2
Breakdown Voltage	V_{BR}	6		9	V	$I_T = 1\text{mA}$, pin 1 or pin 2 to pin 3 and between pin 1 and pin 2
Reverse Leakage Current	I_R			0.06	μA	$V_{RWM} = 5\text{V}$, pin 1 or pin 2 to pin 3 and between pin 1 and pin 2
Clamping Voltage	V_C			10	V	$I_{PP} = 2\text{A}$ ($8 \times 20\mu\text{s}$ pulse), pin 1 to pin 3 or pin 2 to pin 3
Junction Capacitance	C_J		0.6		pF	$V_R = 0\text{V}$, $f = 1\text{MHz}$, pin 1 or pin 2 to pin 3
Junction Capacitance	C_J		0.35		pF	$V_R = 0\text{V}$, $f = 1\text{MHz}$, pin 1 to pin 2

Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)

Fig1. 8/20 μs Pulse Waveform

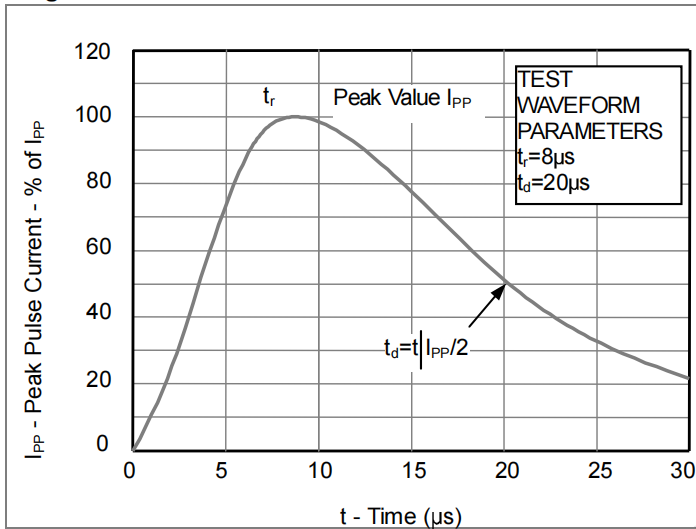


Fig2. ESD Pulse Waveform (according to IEC 61000-4-2)

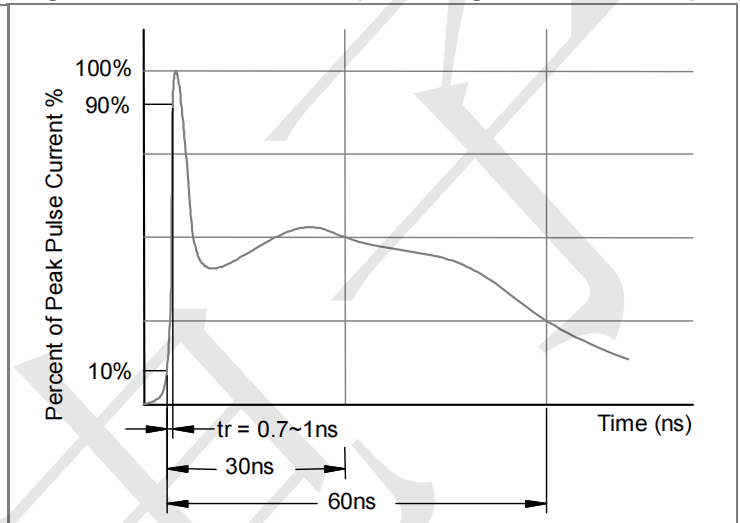
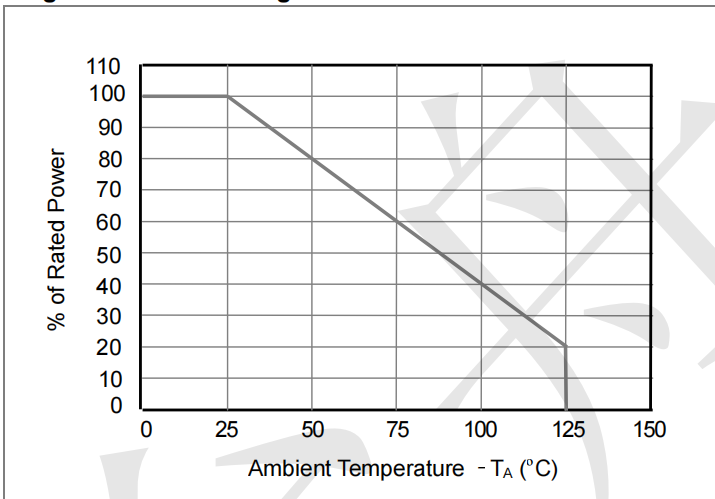
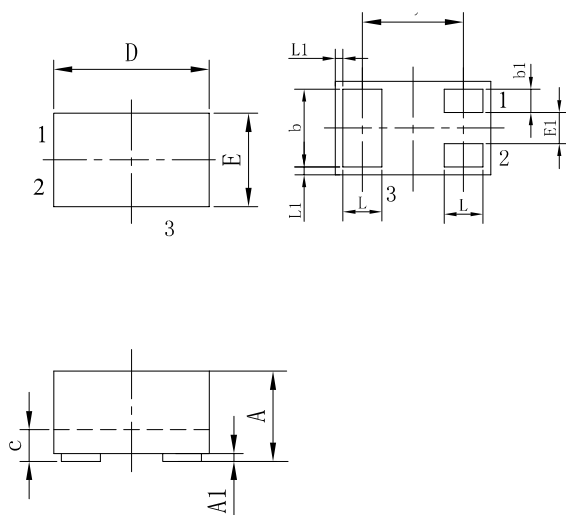


Fig3. Power Derating Curve

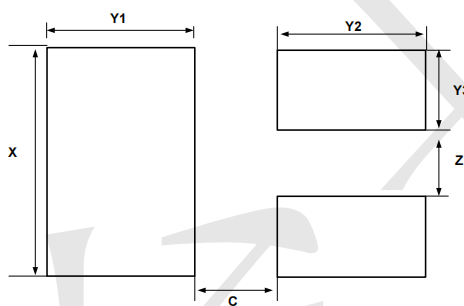


Outline Drawing - DFN1006-3



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
b1	0.10	0.15	0.20	0.004	0.006	0.008
c	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.65 BSC			0.026 BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
E1	0.15	0.20	0.25	0.006	0.008	0.010
L	0.20	0.25	0.30	0.008	0.010	0.012
L1	0.05 REF			0.0002 REF		

Land Pattern -DFN1006-3



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
C	0.25	0.010
X	0.65	0.024
Y1	0.50	0.020
Y2	0.50	0.020
Y3	0.25	0.010
Z	0.20	0.008